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# HZM6.2ZFA

Silicon Epitaxial Planar Zener Diode for Surge Absorb

# HITACHI

ADE-208-593 (Z)  
Rev 0

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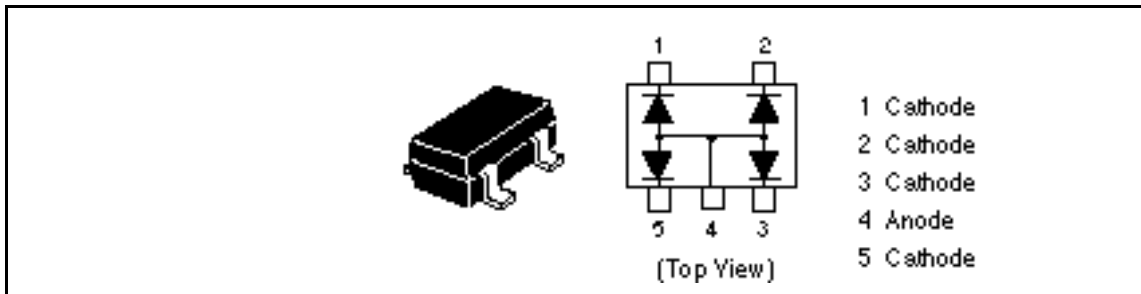
## Features

- Σ HZM6.2ZFA has four devices, and can absorb external + and -surge.
- Σ Low capacitance ( $C = 8.5\text{pF}$  max) and can protect ESD of signal line.
- Σ MPAK-5 package is suitable for high density surface mounting and high speed assembly.

## Ordering Information

| Type No.  | Laser Mark | Package Code |
|-----------|------------|--------------|
| HZM6.2ZFA | 62Z        | MPAK-5       |

## Outline



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## HZM6.2ZFA

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### Absolute Maximum Ratings (Ta = 25°C)

| Item                 | Symbol           | Value       | Unit |
|----------------------|------------------|-------------|------|
| Power dissipation    | Pd <sup>*1</sup> | 200         | mW   |
| Junction temperature | Tj               | 150         | °C   |
| Storage temperature  | Tstg             | -55 to +150 | °C   |

Note: 1. Four device total, See Fig.2.

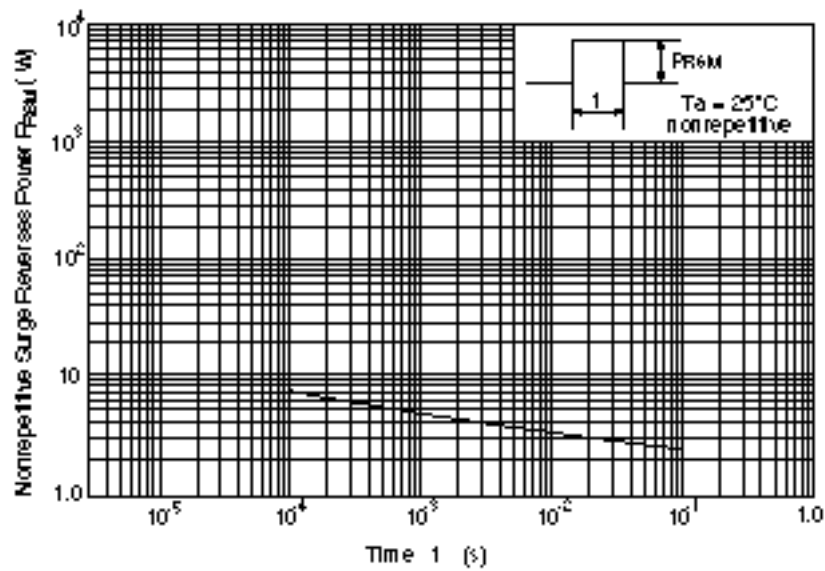
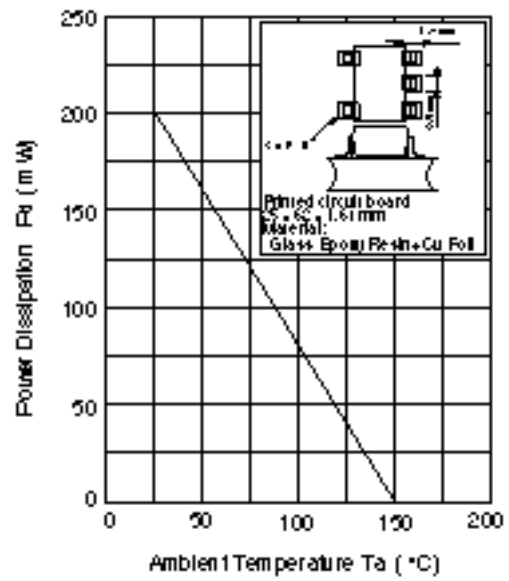
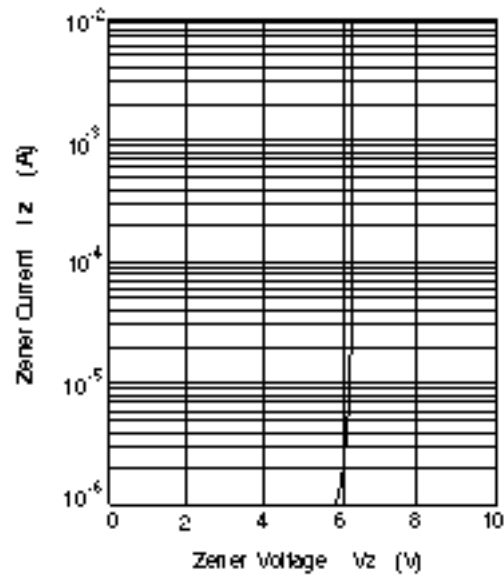
### Electrical Characteristics (Ta = 25°C) <sup>\*1</sup>

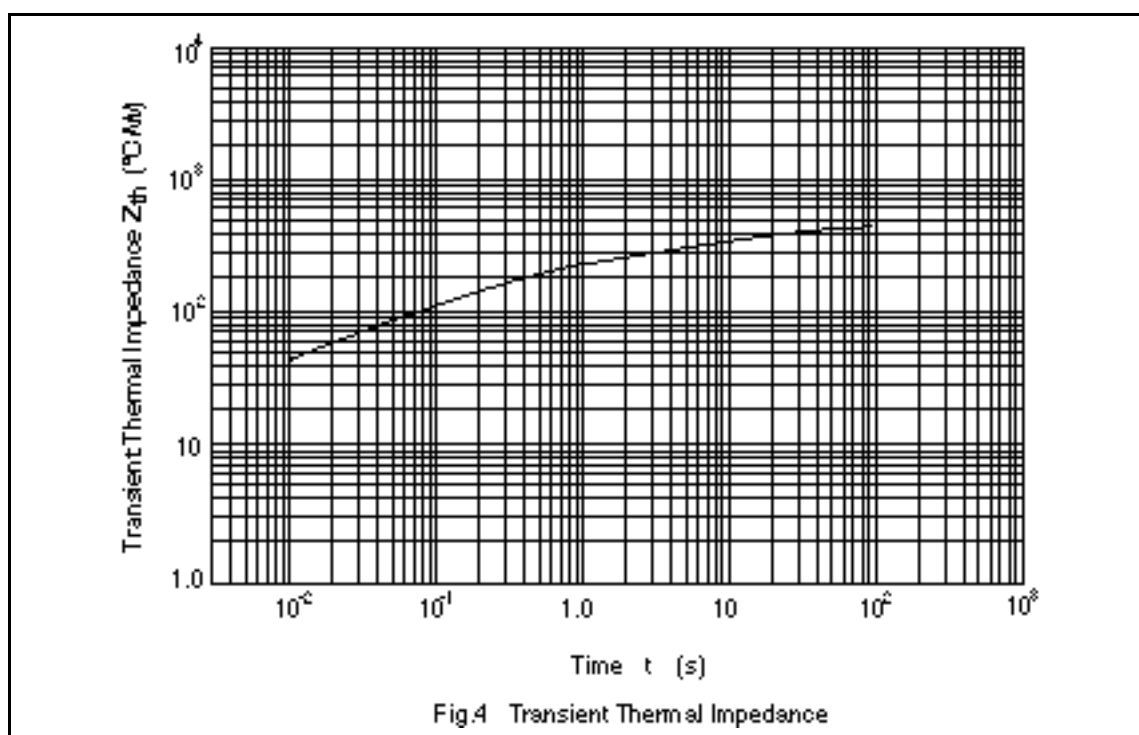
| Item                         | Symbol         | Min  | Typ | Max  | Unit | Test Condition                                                    |
|------------------------------|----------------|------|-----|------|------|-------------------------------------------------------------------|
| Zener voltage                | V <sub>z</sub> | 5.90 | —   | 6.50 | V    | I <sub>z</sub> = 5 mA, 40ms pulse                                 |
| Reverse current              | I <sub>R</sub> | —    | —   | 3    | mA   | V <sub>R</sub> = 5.5 V                                            |
| Capacitance                  | C              | —    | 8.0 | 8.5  | pF   | V <sub>R</sub> = 0 V, f = 1 MHz                                   |
| Dynamic resistance           | r <sub>d</sub> | —    | —   | 60   | W    | I <sub>z</sub> = 5 mA                                             |
| ESD-Capability <sup>*2</sup> | —              | 13   | —   | —    | kV   | C =150 pF, R = 330 W, Both forward and reverse direction 10 pulse |

Notes: 1. Per one device.

2. Failure criterion ; I<sub>R</sub> ≥ 3 mA at V<sub>R</sub> = 5.5 V.

# Main Characteristic



**Main Characteristic (cont)**

Package Dimensions

Unit : mm

